



MMBT9018

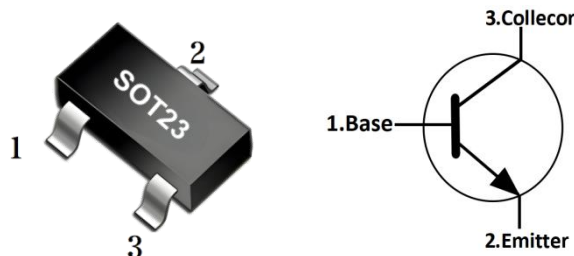
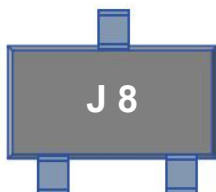
NPN SILICON TRANSISTOR

FEATURES

- *High Current Gain Bandwidth Product
- *AM/FM Amplifier, Local Oscillator of FM/VHF Tuner

MARKING

Type Code: Marking: J 8



ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
BV _{CBO}	Collector-base voltage	30	V
BV _{CEO}	Collector-emitter voltage	15	V
BV _{EBO}	Emitter-base voltage	5	V
I _C	Collector current	50	mA
P _C	Collector Power Dissipation	200	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-60~150	°C
ROJA	Thermal Resistance From Junction To Ambient	625	°C/W

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cutoff current	I _{CBO}	V _{CB} =12V, I _E =0			0.05	μA
Collector cut-off current	I _{CEO}	V _{CE} =12V, I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =3V, I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1mA	100		200	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =10mA, I _B =1mA			1.4	V
Transition frequency	f _T	V _{CE} =5V, I _C = 5mA, f=400MHz		800		MHz



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■ TYPICAL CHARACTERISTICS

